<u>PATENT</u>

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

olicant: Jerome M. Eldridge et al.

Examiner:

Tu-Tu Ho

Serial No.:

10/081,818

Group Art Unit:

2818

Filed:

February 20, 2002

Docket:

1303.045US1

Title:

ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

01/24/2005 NNGUYEN1 00000025 190743 10081818

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Serial No :10/081,818

Filing Date: February 20, 2002

Title: ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW ASYMMETRICAL TUNNEL BARRIER INTERPOLY

INSULATORS

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

JEROME M. ELDRIDGE ET AL.

By their Representatives,

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Caria L

Dkt: 1303.045US1

Date

Timothy B Clise

Reg. No. 40,957

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this day of January, 2005.

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Signatur

PTO/SB/08A(10-01)
Approved for use through 10/31/2002, OMB 651-0031
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)

Complete if Known **Application Number** 10/081,818 February 20, 2002 **Filing Date** Eldridge, Jerome **First Named Inventor** 2818 **Group Art Unit** Ho, Tu-Tu **Examiner Name**

Sheet 1 of 1

Attorney Docket No: 1303.045US1

-	V. W. III		ATENT DOCUMENTS	
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
	US-4,688,078	08/18/1987	Hseih, Ning	12/11/1985
	US-4,939,559	07/03/1990	DiMaria, D. J., et al.	04/01/1986
	US-5,474,947	12/12/1995	Chang, K., et al.	12/27/1993
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	US-6,754,108	06/22/2004	Forbes, L.	08/30/2001

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T²	

OTHER DOCUMENTS NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s),	T²	
		publisher, city and/or country where published.		

N 10/081,818 PATENT

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ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW

ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

Serial/Patent No. 10/929916	Filing Date August 30, 2004	Attorney Docket 1303.035US2	Title PROGRAMMABLE ARRAY LOGIC OR MEMORY WITH P-CHANNEL DEVICES AND ASYMMETRICAL TUNNEL BARRIERS
10/931704	September 1, 2004	1303.014US2	FLASH MEMORY WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS
10/929986	August 30, 2004	1303.045US2	ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS
10/931711	September 1, 2004	1303.029US2	PROGRAMMABLE MEMORY ADDRESS AND DECODE CIRCUITS WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS
10/931540	August 31, 2004	1303.020US2	PROGRAMMABLE ARRAY LOGIC OR MEMORY DEVICES WITH ASYMMETRICAL TUNNEL BARRIERS

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 10/081,818 Filing Date: February 20, 2002

Title: ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS

Respectfully submitted,

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By Applicants' Representatives,

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Dkt: 1303.045US1

Date 14 Jan 05

Reg. No. 40,957

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this ______ day of January, 2005. Navio Loe Signature